

MC74VHCT157A

Quad 2-Channel Multiplexer

The MC74VHCT157A is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable (\bar{E}) inputs. When \bar{E} is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V because it has full 5.0 V CMOS level output swings.

The VHCT157A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage-input/output voltage mismatch, battery backup, hot insertion, etc.

The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

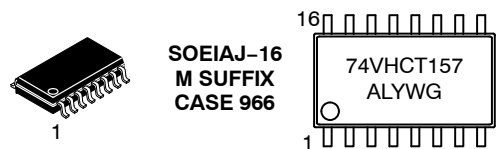
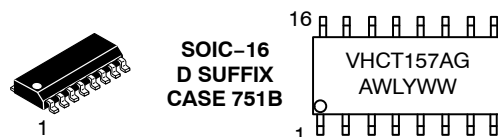
- High Speed: $t_{PD} = 4.1$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 4$ μ A (Max) at $T_A = 25^\circ$ C
- TTL-Compatible Inputs: $V_{IL} = 0.8$ V; $V_{IH} = 2.0$ V
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
 - Human Body Model > 2000 V;
 - Machine Model > 200 V
- Chip Complexity: 82 FETs or 20 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



A = Assembly Location
 WL, L = Wafer Lot
 Y = Year
 WW, W = Work Week
 G or \blacksquare = Pb-Free Package
 (Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Outputs
\bar{E}	S	Y0 - Y3
H	X	L
L	L	A0 - A3
L	H	B0 - B3

A0 - A3, B0 - B3 = the levels of the respective Data-Word Inputs.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC74VHCT157A

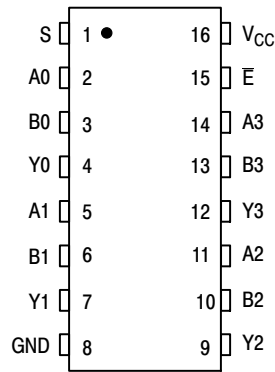


Figure 1. Pin Assignment

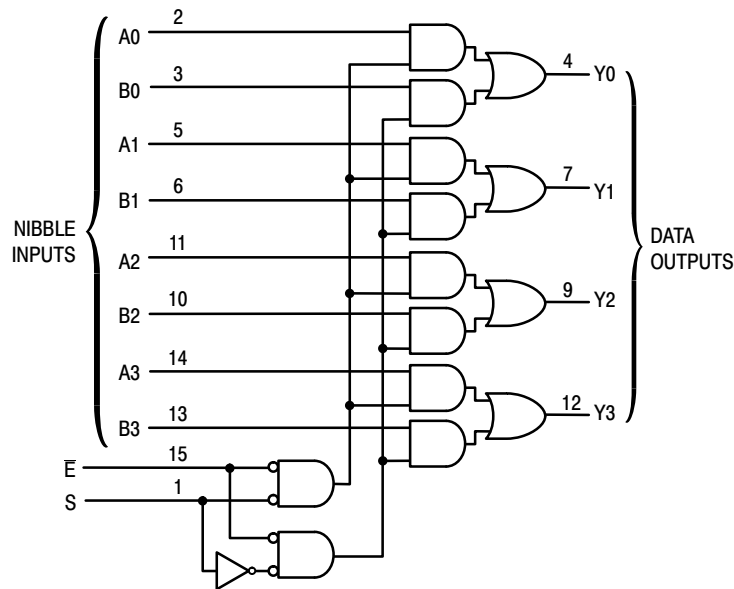


Figure 2. Expanded Logic Diagram

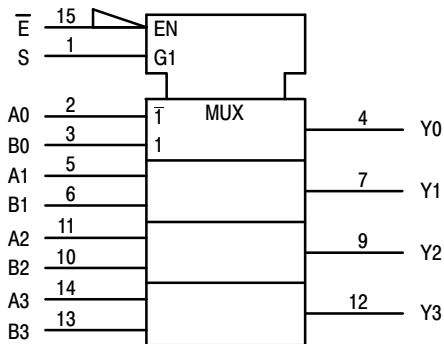


Figure 3. IEC Logic Symbol

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

MC74VHCT157A

MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	Digital Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	Output in 3-State High or Low State -0.5 to +7.0 -0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
I _{OUT}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air	SOIC Package TSSOP 200 180	mW
T _{STG}	Storage Temperature Range	-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4) >2000 >200 >2000	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±300 mA
θ _{JA}	Thermal Resistance, Junction-to-Ambient	SOIC Package TSSOP 143 164	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.
2. Tested to EIA/JESD22-A114-A
3. Tested to EIA/JESD22-A115-A
4. Tested to JESD22-C101-A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage	Output in 3-State High or Low State 0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types	-55	125	°C
t _r , t _f	Input Rise or Fall Time	V _{CC} = 5.0 V ± 0.5 V	0	20 ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

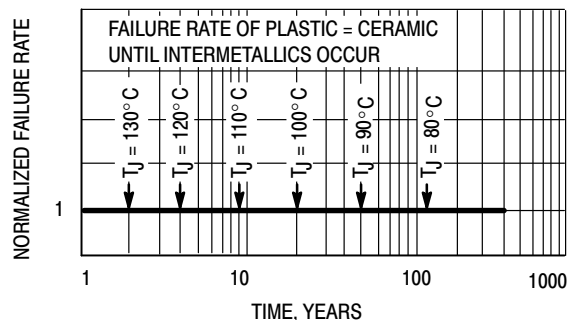


Figure 4. Failure Rate vs. Time Junction Temperature

MC74VHCT157A

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2			2	0.8	2		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V _{OH}	Maximum High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	4.5	4.4	4.5		4.4		4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -8 mA	4.5	3.94			3.8		3.66		V
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	4.5		0.0	0.1		0.1		0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = 8 mA	4.5			0.36		0.44		0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μA
I _{CCT}	Additional Quiescent Supply Current (per Pin)	Any one input: V _{IN} = 3.4 V All other inputs: V _{IN} = V _{CC} or GND	5.5			1.35		1.5		1.5	μA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5		5	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; A to B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF		5.6	7.0	1.0	7.7	1.0	7.7	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 50pF		8.0	10.0	1.0	11.0	1.0	11.0	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; A to B to Y	V _{CC} = 5.0 ± 0.5 V C _L = 15pF		4.1	6.4	1.0	7.5	1.0	7.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 50pF		5.6	8.4	1.0	9.5	1.0	9.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; S to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF		6.1	7.5	1.0	8.2	1.0	8.2	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 50pF		8.5	10.5	1.0	11.5	1.0	11.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; S to Y	V _{CC} = 5.0 ± 0.5 V C _L = 15pF		5.3	8.1	1.0	9.5	1.0	9.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 50pF		6.8	10.1	1.0	11.5	1.0	11.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; E to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15pF		6.1	7.5	1.0	8.2	1.0	8.2	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 50pF		8.5	10.5	1.0	11.5	1.0	11.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay; E to Y	V _{CC} = 5.0 ± 0.5 V C _L = 15pF		5.6	8.6	1.0	10.0	1.0	10.0	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 50pF		7.1	10.6	1.0	12.0	1.0	12.0	
C _{IN}	Maximum Input Capacitance			4	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		Min	Max	
			20	

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 5.0 V)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

MC74VHCT157A

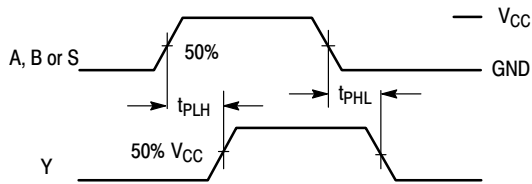


Figure 5. Switching Waveform

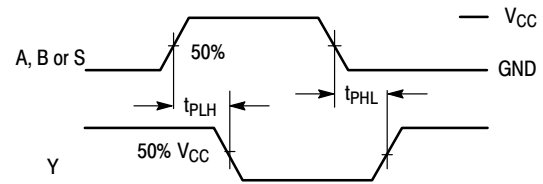
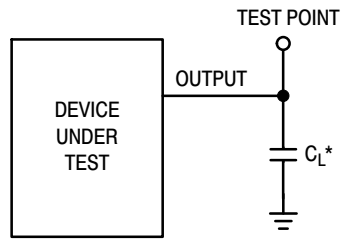


Figure 6. Inverting Switching



*Includes all probe and jig capacitance

Figure 7. Test Circuit

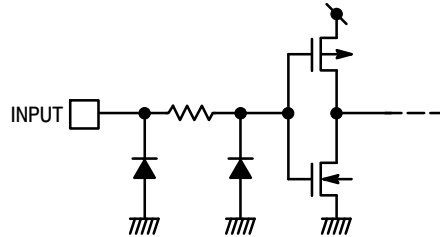


Figure 8. Input Equivalent Circuit

ORDERING INFORMATION

Device	Package	Shipping†
MC74VHCT157ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74VHCT157ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74VHCT157ADTG	TSSOP-16*	96 Units / Rail
M74VHCT157ADTR2G	TSSOP-16*	2500 Tape & Reel
MC74VHCT157AMG	SOEIAJ-16 (Pb-Free)	50 Units / Rail
MC74VHCT157AMELG	SOEIAJ-16 (Pb-Free)	2000 Tape & Reel

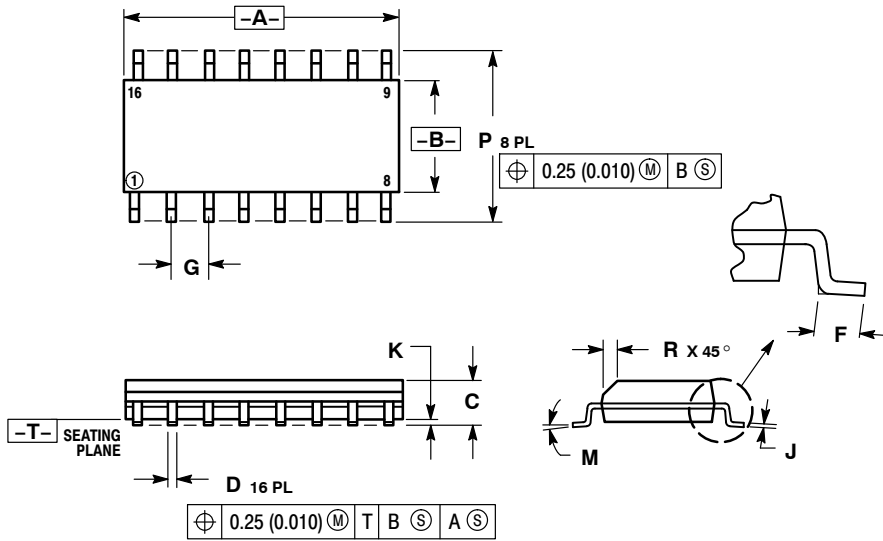
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

MC74VHCT157A

PACKAGE DIMENSIONS

SOIC-16
CASE 751B-05
ISSUE K

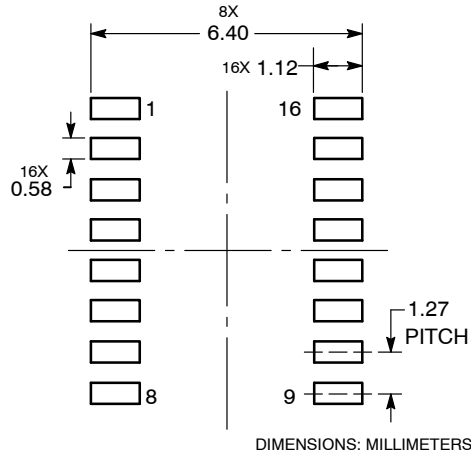


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

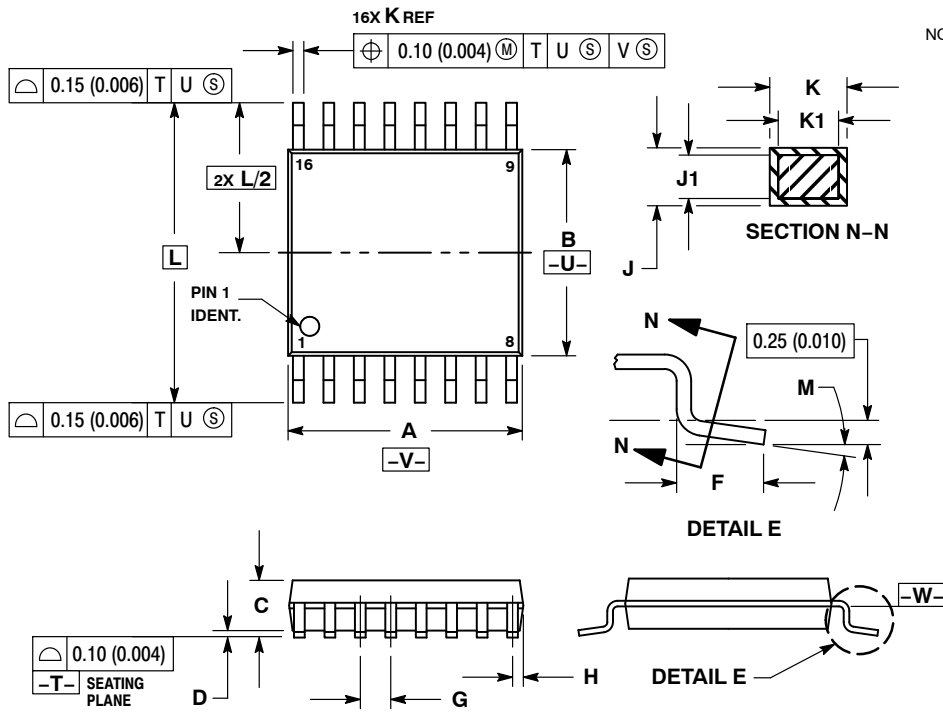
SOLDERING FOOTPRINT



MC74VHCT157A

PACKAGE DIMENSIONS

TSSOP-16
CASE 948F-01
ISSUE B

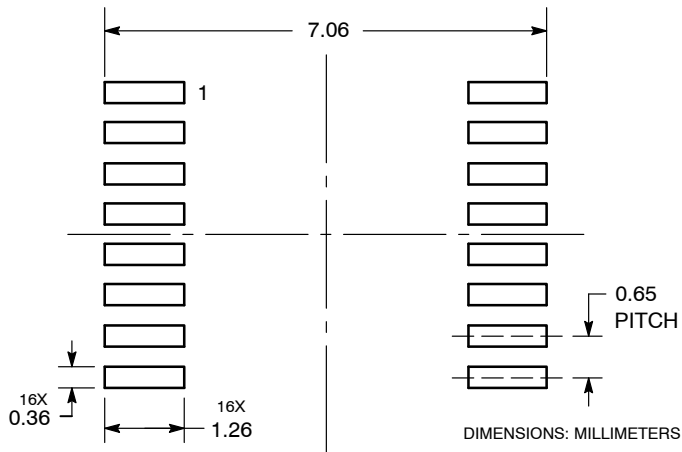


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE $-W-$.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

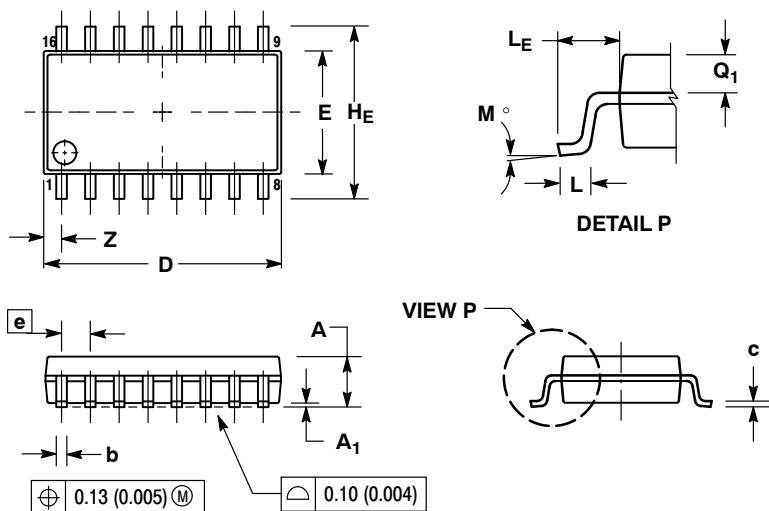
SOLDERING FOOTPRINT



MC74VHCT157A

PACKAGE DIMENSIONS

SOEIAJ-16
CASE 966-01
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

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